# October 22 (Thu.), 2026

## [Oral 10] CMP Fundamentals

09:45-11:10

International Conference Hall (B1F)

● Session Chair: Xinchun Lu (Tsinghua Univ., China)

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| 09:45-10:10<br>[Oral 10-1] | **[Invited]** Research on Atomic-scale Tribochemistry Underlying Wafer-Scale Global Planarization of Advanced Integrated Circuits<br><br>Lifei Zhang, Xinchun Lu (Tsinghua Univ., China), Knut Christoph Gottfried, and Jinji Luo-Hofmann (Fraunhofer Inst. for Electronic Nano Systems ENAS, Germany) |
| 10:10-10:30<br>[Oral 10-2] | Clarification of Polishing Mechanism Focusing on Abrasive Particle Behavior in CMP - Relationship between Abrasive Particle Behavior and Pad Surface Topography in Micro Replicated CMP Pad -<br><br>Haruto Kurokawa, Yoji Oyama, Syuhei Kurokawa,Terutake Hayashi, Keisuke Osawa (Kyushu Univ., Japan), Hirokuni Hiyama, Yutaka Wada, Naoyuki Handa, and Syuntaro Hayashi (Ebara Corp., Japan) |
| 10:30-10:50<br>[Oral 10-3] | Micro-Structured Pads for High-MRR and Low-Damage Oxide Chemical Mechanical Polishing<br><br>Seounghee Yun, Hyun Jun Ryu, Hyeongmin Je, and Sanha Kim (KAIST, Korea) |
| 10:50-11:10<br>[Oral 10-4] | Physics-Informed Friction Coefficient Distribution Modeling for Material Removal Rate Prediction in Chemical Mechanical Polishing<br><br>Sho Hirono (Kobe Univ., Japan), Chihiro Mitani (Chuo Univ., Japan), Takumi Sato, Kodai Hirano (Ebara Corp., Japan), and Norikazu Suzuki (Kobe Univ., Japan) |